

Type	Hits	Search Text	DBs	Time Stamp
Per	1	BRS 0 ((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	USPAT	2001/03/19
Acti	2	BRS 1 ((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	USPAT	2001/03/19
Fail	3	BRS 0 ((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	EPO; JPO; DERWENT; IBM	2001/03/19
Sav	4	BRS 11 (((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	EPO; JPO; DERWENT; IBM	2001/03/20
	5	BRS 28 (((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$)) ) and ((semic	USPAT	2001/03/20
	6	BRS 17 (((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$)) ) and ((semi	USPAT	2001/03/20
	7	BRS 16 halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))	USPAT	2001/03/20
	8	BRS 1 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20
	9	BRS 1 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20
	10	BRS 13 (semiconductor adj device) and ((nitrogen adj concentration) with oxynitride)	USPAT	2001/03/20
	11	BRS 1 (halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20
	12	BRS 11 ((halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectr	USPAT	2001/03/20
	13	BRS 1 5869858.bn.	USPAT	2001/03/20
	14	BRS 1 5866930.bn.	USPAT	2001/03/20
	15	BRS 1 5831319.bn.	USPAT	2001/03/20
	16	BRS 1 5814863.bn.	USPAT	2001/03/20
	17	BRS 1 5753564.bn.	USPAT	2001/03/20
	18	BRS 0 ((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and ((insulating or dielectric) adj film)).ab	USPAT	2001/03/20
	19	BRS 0 ((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and (insulating or dielectric)).ab.	USPAT	2001/03/20
	20	BRS 0 ((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and (insulating or dielectric)).clm.	USPAT	2001/03/20
	21	BRS 0 (((halogen or fluor\$) and (nitrogen or nitride).and (silicon) and (oxy\$) and (insulating or dielectric))).and (semi	USPAT	2001/03/20
	22	BRS 0 (((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and (insulating or dielectric))) and (semi	USPAT	2001/03/20
	23	BRS 8 (halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectric))	EPO; JPO; DERWENT; IBM	2001/03/20
	24	BRS 0 (nitrogen adj concentration) with ((insulating or dielectric) adj film)	US-PGPUB	2001/03/20
	25	BRS 2 (semiconductor adj device).ti.	US-PGPUB	2001/03/20
	26	BRS 4 ((nitrogen adj concentration) with ((insulating or dielectric) adj film)) and (halogen or fluor\$)	USPAT	2001/03/20
	27	BRS 15 (atomic adj percent) same (atomic adj concentration)	USPAT	2001/03/21
	28	BRS 1 6191463.bn.	USPAT	2001/03/21
	29	BRS 25 ((gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)) and (nitrogen with conce	USPAT	2001/09/20
	30	BRS 1 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/09/21
	31	BRS 2 (halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	EPO; JPO; DERWENT; IBM	2001/09/21
	32	BRS 34 (halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectric))	USPAT	2001/09/21
	33	BRS 2 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/09/21
	34	BRS 2 (halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	EPO; JPO; DERWENT; IBM	2001/09/22
	35	BRS 36 (gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)	USPAT	2001/09/22
	36	BRS 36 (gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)	USPAT	2001/09/22
	37	BRS 5 ((gate adj (insulator or dielectric or insulating)) with (halide or halogen or fluorine or bromine or chlorine or iod	USPAT	2001/09/23
	38	BRS 36 ((gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping))	USPAT	2001/09/23
	39	BRS 0 ((spacer) with (source or drain)) and ("JP 11111845 A".DID. and (((gate adj insulator) or dielectric) with ((sil	USPAT	2001/09/23
	40			

Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Detail	Errors
File	1	Search					

Type	Hk#	Search Text	DBs	Time Stamp
Dra				
Per	40	((spacer) with (source or drain) and (((source or drain) with (beside) with (gate)))	USPAT	2001/09/23
Act	41	((spacer with (source or drain) with polysilicon) not ((ldd or (lightly adj doped).ab.)) and ("spacer is drain")	USPAT	2001/09/23
Fail	42	((spacer with (source or drain) with polysilicon) not ((ldd or (lightly adj doped).ab.)) and ("spacer is" adj (dra	USPAT	2001/09/23
Env	43	((lateral with transistor) and (spacer with polysilicon) not ((bipolar or bj).ab.)) and ((source or drain) with ab	USPAT	2001/09/23
(	44	((lateral with transistor) and (spacer with polysilicon) not ((bipolar or bj).ab.)) and ((source or drain) with ab	USPAT	2001/09/23
(	45	((lateral with transistor) and (spacer with (polysilicon or silicon))) not ((bipolar or bj).ab.)) and ((source or dr	USPAT	2001/09/23
(	46	((lateral with transistor) and (spacer with (polysilicon or silicon))) not ((bipolar or bj).ab.)) and ((source or dr	USPAT	2001/09/23
(	47	(polysilicon adj (drain or source) adj spacer)	USPAT	2001/09/23
(	48	(silicon adj (drain or source) adj spacer)	USPAT	2001/09/23
(	49	((silicon adj (drain or source)) with spacer)	USPAT	2001/09/23
(	50	((raised or elevated adj (source or drain)) not ((soi or (silicon adj on adj insulator).ab)) and ((polysilicon or s	USPAT	2001/09/23
(	51	(morosawa and narihiro).in.	DERWENT	2001/09/23
(	52	(morosawa).in.	DERWENT	2001/09/23
(	53	3923559.pn.	USPAT	2001/09/23
(	54	(nitrogen with concentration) with ("cm.sub.") with (gate adj (insulation or insulator or dielectric))	USPAT	2001/09/23
(	55	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric)))	USPAT	2001/09/23
(	56	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) same ("cm.sub.")	USPAT	2001/09/23
(	57	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) same ("cm.sup.")	USPAT	2001/09/23
(	58	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) and (nitrogen with ("cm.sup	USPAT	2001/09/23
(	59	6191463.pn. and (concentration)	USPAT	2001/09/23
(	60	6191463.pn. and (nitrogen)	USPAT	2001/09/23
(	61	4016587.pn.	USPAT	2001/09/23
(	62	"4016587"	USPAT	2002/01/14
(	63	(diffusion adj width) and (gate adj width)	USPAT	2002/01/14
(	64	(diffusion adj width) with different	USPAT	2002/01/14
(	65	(diffusion adj width) with (minimize)	USPAT	2002/01/14
(	66	(diffusion adj width) with (minimal)	USPAT	2002/01/14
(	67	(diffusion adj width) with (reduce)	USPAT	2002/01/14
(	68	array and ((diffusion adj width) with (area))	USPAT	2002/01/14
(	69	(diffusion adj width) with (area)	USPAT	2002/01/14
(	70	(diffusion adj width) with (area)	US-PGPUB; EPO; JPO; DE	2002/01/14
(	71	(channel adj width) with (area) with (fox or (field adj (oxide or oxidation))) with (reduce or decrease or minimiz	US-PGPUB; EPO; JPO; DE	2002/01/14
(	72	(channel adj width) with (area) with (fox or (field adj (oxide or oxidation))) with (reduce or decrease or minimiz	USPAT	2002/01/14
(	73	(dense or denser) and ((channel adj width) with (area) with (reduce or decrease or minimize))	USPAT	2002/01/14
(	74	"5053840".PN.	USPAT	2002/01/14
(	75	"4377818".PN.	USPAT	2002/01/14
(	76	"4630085".PN.	USPAT	2002/01/14
(	77	"4763177".PN.	USPAT	2002/01/14
(	78	(integration) and ((channel adj width) with (area) with (reduce or decrease or minimize))	USPAT	2002/01/14

Type	Hk#	Search Text	DBs	Time Stamp	Comments	Error Defined	Errors
Patent	79						

SEARCH RESULTS

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Type	Hits	Search Text	DBs	Time Stamp
Per	79	BRS 0 (cmos with (gate adj array)) and (denser) and (channel adj width)	USPAT	2002/01/14
Act	80	BRS 10 (cmos with (gate adj array)) and ((area) with (channel adj width))	USPAT	2002/01/14
Fail	81	"5285069"	USPAT	2002/01/14
Sav	82	BRS 4 "5629548"	USPAT	2002/01/14
	83	BRS 5 adjustable adj gate adj width	USPAT	2002/01/14
	84	BRS 0 (master adj slice) and (width with (change or changed or adjust or adjusted or reduce or reduced or decrease	USPAT	2002/01/14
	85	BRS 1 (master adj slice) and (width with (change or changed or adjust or adjusted or reduce or reduced or decrease	USPAT	2002/01/14
	86	BRS 12 (master adj slice) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduce	US-PGPUB; EPO; JPO; DE	2002/01/14
	87	BRS 10 (master adj slice) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduce	USPAT	2002/01/14
	88	BRS 3 (gate adj array) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduced	USPAT	2002/01/14
	89	BRS 1 (gate adj array) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduced	US-PGPUB; EPO; JPO; DE	2002/01/14
	90	BRS 2 ((gate adj array) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduced	USPAT	2002/03/02
	91	BRS 15 (narihiro and morosawa).in.	JPO	2002/03/02
	92	BRS 6 "5821172"	USPAT	2002/03/02
	93	BRS 5 "5821172" and nitrogen	USPAT	2002/03/02
	94	BRS 3 "5821172" and (nitrogen with concentration)	USPAT	2002/03/02
	95	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with halogen with ("F" or fluorine or fluori	USPAT	2002/03/07
	96	BRS 5 (morosawa and iwata).in.	JPO; DERWENT	2002/03/07
	97	BRS 7 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	98	BRS 24 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and con	USPAT	2002/03/07
	99	BRS 35 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride))	USPAT	2002/03/07
	100	BRS 7 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and am	USPAT	2002/03/07
	101	BRS 23 ((n or nitrogen) with { atomic or at) with ("% or percent or percentage)) and (((silicon adj (oxide or dioxide)) o	USPAT	2002/03/07
	102	BRS 1 6191463.pn.	USPAT	2002/03/07
	103	BRS 0 6191463.pn. and (nitrogen with boron)	USPAT	2002/03/07
	104	BRS 1 6191463.pn. and (nitrogen same boron)	USPAT	2002/03/07
	105	BRS 1 6191463.pn. and (nitrogen)	USPAT	2002/03/07
	106	BRS 1 6191463.pn. and (nm)	USPAT	2002/03/07
	107	BRS 6 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	108	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	109	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	110	BRS 1 "6191463"	USPAT	2002/03/07
	111	BRS 30 ((doping adj concentration) with approximately) and (substrate.clm.) and "2001"	USPAT	2002/03/07
	112	BRS 7 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	113	BRS 1 "4755865".PN.	USPAT	2002/03/07
	114	BRS 1 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	115	BRS 12 ("4755865"	USPAT	2002/03/07
	116	BRS 14 ("4755865"	USPAT	2002/03/07
	117	BRS 1 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/08

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SEARCH RESULTS

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Per 118 BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT

Act 119 BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT

Fail 120 BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT

Sav 121 BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT

Log 122 BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT

Err 123 BRS 15 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT

124 BRS 0 10-365861.did. JPO; DERWENT 2002/03/10

125 BRS 0 10365861.did. JPO; DERWENT 2002/03/10

126 BRS 5 (narihiro and morosawa and iwata).in. JPO 2002/03/10

127 BRS 5 (narihiro and morosawa and iwata).in. JPO; DERWENT 2002/03/10

128 BRS 5 (narihiro and morosawa and iwata).in. JPO; DERWENT 2002/03/10

129 BRS 5 ( morosawa and iwata).in. JPO; DERWENT 2002/03/10

130 BRS 11 (iwata).in. and (sharp.as.) and nitrogen JPO; DERWENT 2002/03/10

131 BRS 3 (morosawa).in. and (sharp.as.) and nitrogen JPO; DERWENT 2002/03/10

132 BRS 0 (maximum adj concentration) with nitrogen with (gate adj (oxide or dielectric or insulator or insulating or insulation)) USPAT 2002/03/10

133 BRS 5 (maximum adj concentration) with (gate adj (oxide or dielectric or insulator or insulating or insulation)) USPAT 2002/03/10

134 BRS 1 "4085498".PN. USPAT 2002/03/10

135 BRS 1 (" 4085498" USPAT 2002/03/10

136 BRS 4 (" 4085498" USPAT 2002/03/10

137 BRS 1 "6013553".PN. USPAT 2002/03/10

138 BRS 1 "6140024".PN. USPAT 2002/03/10

139 BRS 1 "5567638".PN. USPAT 2002/03/10

140 BRS 18 (high adj concentration) with nitrogen with (gate adj (oxide or dielectric or insulator or insulating or insulation)) USPAT 2002/03/10

141 BRS 31 "5567638" USPAT 2002/03/10

142 BRS 12 "5567638" and (nitrogen with concentration) USPAT 2002/03/10

143 BRS 5 "5674788" and ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concent USPAT 2002/03/10

144 BRS 1 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and ( USPAT 2002/03/10

145 BRS 35 nitrogen with "1.times.10.sup.21" USPAT 2002/03/10

146 BRS 8 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and ( USPAT 2002/03/10

147 BRS 37 nitrogen with "1.times.10.sup.20" USPAT 2002/03/10

148 BRS 0 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and ( USPAT 2002/03/10

149 BRS 6 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and ( USPAT 2002/03/10

150 BRS 14 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj implant)) USPAT 2002/03/10

151 BRS 4 nitrogen with "1.times.10.sup.22" USPAT 2002/03/10

152 BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo USPAT 2002/03/10

153 BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo USPAT 2002/03/10

154 BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo USPAT 2002/03/10

155 BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo USPAT 2002/03/10

156 BRS 15 "5571734" USPAT 2002/03/10

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118 BRS 0 10-365861.did. JPO; DERWENT 2002/03/10

Type	Text	Search Text	DBs	Date
Per	BRS 12	"5571734" and concentration	USPAT	2002/03/10
Act	BRS 8	"5571734" and (concentration with (nitrogen or fluorine))	USPAT	2002/03/10
Fail	BRS 4	(* "4016587")	USPAT	2002/03/11
Sav	BRS 1	(6191463.pn.) and boron	USPAT	2002/03/11
(I)	BRS 1	(6191463.pn.) and nitrogen	USPAT	2002/03/11
(C)	BRS 2	"5674788" and fluorine	USPAT	2002/03/11
(C)	BRS 2	"5674788" and fluorine and nitrogen	USPAT	2002/03/11
(C)	BRS 1	"5674788.pn. and thickness	USPAT	2002/03/11
(C)	BRS 5	"5674788" and nm	USPAT	2002/03/11
(C)	BRS 1	5397720.pn.	USPAT	2002/03/11
(C)	BRS 20	"5397720" and (angstrom or nm)	USPAT	2002/03/11
(C)	BRS 11	((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitridation) and ((gate adj (oxide or insu	USPAT	2002/09/11
(C)	BRS 8	((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitrided) and ((gate adj (oxide or insu	USPAT; US-PGPUB	2002/09/11
(C)	BRS 27	((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitride )and (fluorine with (channel or	USPAT; US-PGPUB	2002/09/11
(C)	BRS 1	"5940699".PN.	USPAT	2002/09/11
(C)	BRS 22	(fluorine with gate with order)	USPAT; US-PGPUB	2002/09/12
(C)	BRS 27	(fluorine with gate) and (fluorine with (injected or injection))	USPAT; US-PGPUB	2002/09/12
(C)	BRS 8	((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitride )and (fluorine with (channel or	USPAT; US-PGPUB	2003/05/07
(C)	BRS 6	(MOROSAWA and NARIHIRO and IWATA and HIROSHI).in.	EPO; JPO; DERWENT; IBM	2003/05/07
(C)	BRS 6	(MOROSAWA and NARIHIRO and IWATA and HIROSHI).in.	EPO; JPO; DERWENT; IBM	2003/05/07
(C)	BRS 15	((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitridation) and ((gate adj (oxide or insu	USPAT; US-PGPUB	2003/05/07
(C)	BRS 10	gate with nitrogen with boron with fluorine	USPAT	2003/05/19
(C)	BRS 2	gate with nitrogen with boron with fluorine	EPO; JPO; DERWENT	2003/05/19
(C)	BRS 0	((fet or transistor).ab.) and ((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (flouri\$)))	USPAT	2003/05/19
(C)	BRS 0	transconductance with boron with diffusion	USPAT	2003/05/19
(C)	BRS 2	((flat adj band) with fluorine) same ((flat adj band) with gate)	USPAT	2003/09/04
(C)	BRS 0	((flat adj band) with fluorine) same ((flat adj band) with gate)	EPO; JPO; DERWENT; IBM	2003/09/04
(C)	BRS 0	((flat adj band) with fluorine) same ((flat adj band) with gate)	EPO; JPO; DERWENT; IBM	2003/09/04
(C)	BRS 2	((flat adj band) with fluorine) same ((flat adj band) with gate)	USPAT	2003/09/04
(C)	BRS 1	((flat adj band) with fluorine) same ((flat adj band) with gate)	US-PGPUB	2003/09/04
(C)	BRS 2	(flat adj band) with fluorine with gate	USPAT	2003/09/04
(C)	BRS 2	(flat adj band) with fluorine with gate	USPAT	2003/09/04
(C)	BRS 1	(flat adj band) with fluorine with gate	US-PGPUB	2003/09/04
(C)	BRS 3	transconductance with fluorine with gate	USPAT	2003/09/04
(C)	BRS 3	transconductance with fluorine with gate	USPAT	2003/09/04
(C)	BRS 0	transconductance with fluorine with gate	US-PGPUB	2003/09/04
(C)	BRS 1	transconductance with boron with gate	USPAT	2003/09/04
(C)	BRS 0	(flat\$1band) with fluorine with gate	USPAT	2003/09/04
(C)	BRS 0	(flat\$1band) with fluorine with gate	USPAT	2003/09/04

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Type	Text	Search Text	DBs	Time Stamp
Per	188 BRS 2 (flat adj band) with fluorine with gate		USPAT	2003/09/04
Act	189 BRS 1 (flat adj band) with fluorine with gate		US-PGPUB	2003/09/04
Fail	190 BRS 3 transconductance with fluorine with gate		USPAT	2003/09/04
Sav	191 BRS 3 transconductance with fluorine with gate		USPAT	2003/09/04
(	192 BRS 0 transconductance with fluorine with gate		US-PGPUB	2003/09/04
)	193 BRS 1 transconductance with boron with gate		USPAT	2003/08/04
(	194 BRS 0 (flat\$1band) with fluorine with gate		USPAT	2003/09/04
)	195 BRS 0 (flat\$1band) with fluorine with gate		USPAT	2003/09/04
(	196 BRS 0 (flat\$1band) with fluorine with gate		US-PGPUB	2003/09/04
)	197 BRS 1 transconductance with boron with gate		USPAT	2003/08/04
(	198 BRS 4 transconductance with boron with gate		US-PGPUB	2003/09/04
)	199 BRS 7 transconductance with threshold with diffusion		USPAT	2003/09/04
(	200 BRS 0 (transconductance with boron with gate ) and (@ad<19991224 or @rlad<19991224)		US-PGPUB	2003/09/04
)	201 BRS 8 transconductance with threshold with diffusion		USPAT	2003/09/04
(	202 BRS 8 (transconductance with threshold with diffusion ) and (@ad<19991224 or @rlad<19991224)		USPAT	2003/09/04
)	203 BRS 16 transconductance with diffusion with gate		USPAT	2003/09/04
(	204 BRS 16 transconductance with diffusion with gate		USPAT	2003/09/04
)	205 BRS 1 transconductance with diffusion with gate		US-PGPUB	2003/09/04
(	206 BRS 21 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
)	207 BRS 0 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(	208 BRS 23 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
)	209 BRS 15 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrided or nitridation) )and (fluorine	USPAT; US-PGPUB	2003/09/04	
(	210 BRS 16 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrided or nitridation) ) and (fluorine	USPAT; US-PGPUB	2003/09/04	
)	211 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(	212 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
)	213 BRS 4 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(	214 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
)	215 BRS 8 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride )and (fluorine with (channel or	USPAT; US-PGPUB	2003/09/04	
(	216 BRS 0 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
)	217 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(	218 BRS 0 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
)	219 BRS 9 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride )and (fluorine with (channel or	USPAT; US-PGPUB	2003/09/04	
(	220 BRS 8 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride )and (fluorine with gate with o	USPAT; US-PGPUB	2003/09/04	
)	221 BRS 10 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride )and (fluorine with gate with o	USPAT; US-PGPUB	2003/09/04	
(	222 BRS 5 "6191463"		USPAT; US-PGPUB	2003/09/04
)	223 BRS 3 "5674788" and (fluorine)		USPAT	2003/09/04
(	224 BRS 3 "5674788" and (fluorine)		USPAT	2003/09/04
)	225 BRS 0 "5674788" and (fluorine)		US-PGPUB	2003/09/04
(	226 BRS 7 "6191463"		USPAT; US-PGPUB	2003/09/04

Type	Text	Search Text	DBs	Time Stamp	Comments	Error Detail	Errors